# TCP-5039UB

# 3.9 pF Passive Tunable Integrated Circuits (PTIC)

### Introduction

ON Semiconductor's PTICs have excellent RF performance and power consumption, making them suitable for any mobile handset or radio application. The fundamental building block of our PTIC product line is a tunable material called ParaScan™, based on Barium Strontium Titanate (BST). PTICs have the ability to change their capacitance from a supplied bias voltage generated by the Control IC. The 3.9 pF ultra−high tuning PTICs are available as wafer−level chip scale packages (WLCSP).

### Key Features

- Ultra−High Tuning Range(5:1) and Operation up to 24 V
- Usable Frequency Range: from 700 MHz to 2.7 GHz
- High Quality Factor (Q) for Low Loss
- High Power Handling Capability
- Compatible with PTIC Control ICs from ON Semiconductor
- These devices are Pb−Free and RoHS Compliant

### Typical Applications

- Multi−band, Multi−standard, Advanced and Simple Mobile Phones
- Tunable Antenna Matching Networks
- Tunable RF Filters
- Active Antennas

ON Semiconductor®

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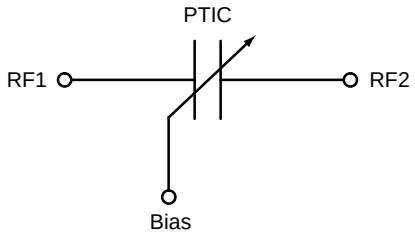
**WLCSP6**
**1.097x0.622**
**CASE 567NZ**

### MARKING DIAGRAM




E = Specific Device Code
Y = Year
W = Work Week

### FUNCTIONAL BLOCK DIAGRAM




**PTIC Functional Block Diagram**

### ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| TCP−5039UB−DT | WLCSP6 (Pb−Free) | 4000 Units / 7" Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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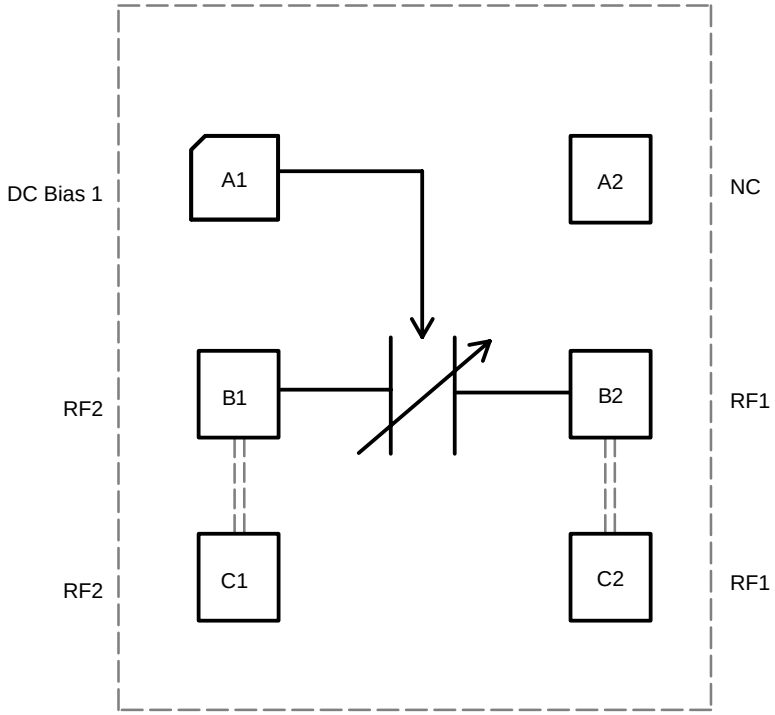



**Figure 1. PTIC Functional Block Diagram**
**(Top View)**

**Table 1. SIGNAL DESCRIPTIONS**

| Ball / Pad Number | Pin Name | Description |
|---|---|---|
| A1 | DC Bias 1 | DC Bias Voltage |
| B1 | RF2 | RF Output |
| C1 | RF2 | RF Output |
| A2 | NC | Not Connected |
| B2 | RF1 | RF Input |
| C2 | RF1 | RF Input |

## TYPICAL SPECIFICATIONS

**Representative Performance Data at 25°C**

**Table 2. PERFORMANCE DATA**

| Parameter | Min | Typ | Max | Unit |
|---|---|---|---|---|
| Operating Bias Voltage | 1.0 | | 24 | V |
| Capacitance ($V_{bias}$ = 2 V) | 3.549 | 3.90 | 4.251 | pF |
| Capacitance ($V_{bias}$ = 24 V) | 0.763 | 0.839 | 0.914 | pF |
| Tuning Range (1 V − 24 V) | 4.80 | 5.25 | 6.00 | |
| Tuning Range (2 V − 24 V) | 4.20 | 4.65 | 5.30 | |
| Leakage Current ($V_{bias}$ = 24 V) | | | 0.1 | μA |
| Operating Frequency | 700 | | 2700 | MHz |
| Quality Factor @ 700 MHz, 2 V (Note 5) | | 65 | | |
| Quality Factor @ 700 MHz, 24 V (Note 5) | | 85 | | |
| Quality Factor @ 2.4 GHz, 2 V (Note 5) | | 45 | | |
| Quality Factor @ 2.4 GHz, 24 V (Note 5) | | 40 | | |
| IP3 ($V_{bias}$ = 2 V) (Notes 1, 3 and 5) | | 70 | | dBm |
| IP3 ($V_{bias}$ = 24 V) (Notes 1, 3 and 5) | | 80 | | dBm |
| 2nd Harmonic ($V_{bias}$ = 2 V) (Notes 2, 3 and 5) | | −65 | | dBm |
| 2nd Harmonic ($V_{bias}$ = 24 V) (Notes 2, 3 and 5) | | −80 | | dBm |
| 3rd Harmonic ($V_{bias}$ = 2 V) (Notes 2, 3 and 5) | | −45 | | dBm |
| 3rd Harmonic ($V_{bias}$ = 24 V) (Notes 2, 3 and 5) | | −75 | | dBm |
| Average Transition Time (Cmin → Cmax) (Notes 4 and 5) | | 66 | | μs |
| Average Transition Time (Cmax → Cmin) (Notes 4 and 5) | | 48 | | μs |

1. $f_1$ = 850 MHz, $f_2$ = 860 MHz, Pin 25 dBm/Tone
2. 850 MHz, Pin +34 dBm
3. IP3 and Harmonics are measured in the shunt configuration in a 50 Ω environment
4. $RF_{IN}$ and $RF_{OUT}$ are both connected to DC ground
5. Sample testing only. Average Transition Time for all start and stop voltage combinations between 2 V and 24 V is 50 μs.

**Representative performance data at 25°C for 3.9 pF WLCSP Package**

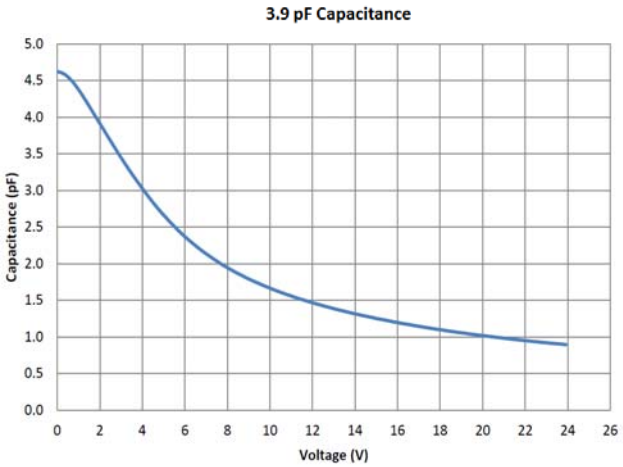



**Figure 2. Capacitance**

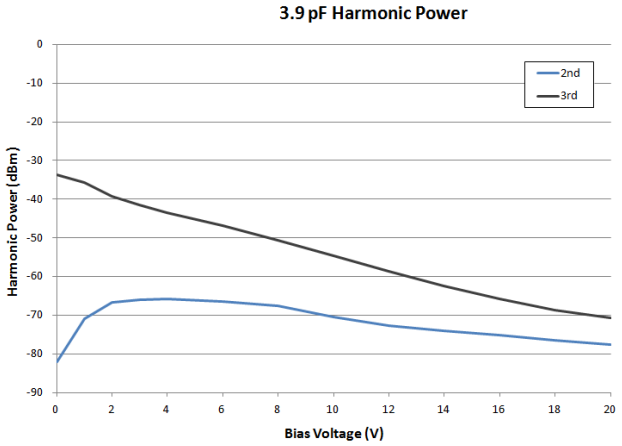



**Figure 3. Harmonic Power***

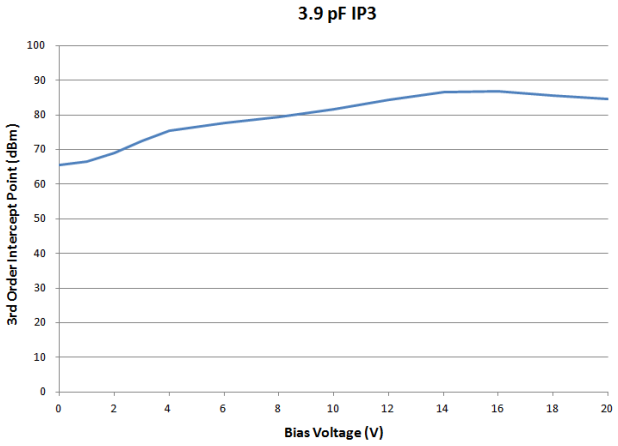



**Figure 4. IP3***

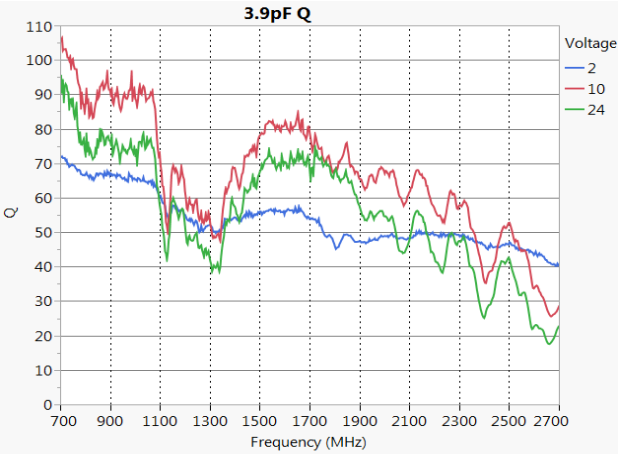



**Figure 5. Q***

*Data shown is representative only.

**Table 3. ABSOLUTE MAXIMUM RATINGS**

| Parameter | Rating | Units |
|---|---|---|
| Input Power | +40 | dBm |
| Bias Voltage | +30 (Note 6) | V |
| Operating Temperature Range | −30 to +85 | °C |
| Storage Temperature Range | −55 to +125 | °C |
| ESD − Human Body Model | Class 1B JEDEC HBM Standard (Note 7) | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

6. WLCSP: Recommended Bias Voltage not to exceed 24 V.
7. Class 1B defined as passing 500 V, but may fail after exposure to 1000 V ESD pulse.

## ASSEMBLY CONSIDERATIONS AND REFLOW PROFILE

The following assembly considerations should be observed:

### Cleanliness

These chips should be handled in a clean environment.

### Electro−static Sensitivity

ON Semiconductor's PTICs are ESD Class 1B sensitive. The proper ESD handling procedures should be used.

### Mounting

The WLCSP PTIC is fabricated for Flip Chip solder mounting. Connectivity to the RF and Bias terminations on the PTIC die is established through SAC305 solder balls with 90 μm nominal height (65 μm to 115 μm height variation). The PTIC die is RoHS−compliant and compatible with lead−free soldering profile.

### Molding

The PTIC die is compatible for over−molding or under−fill.

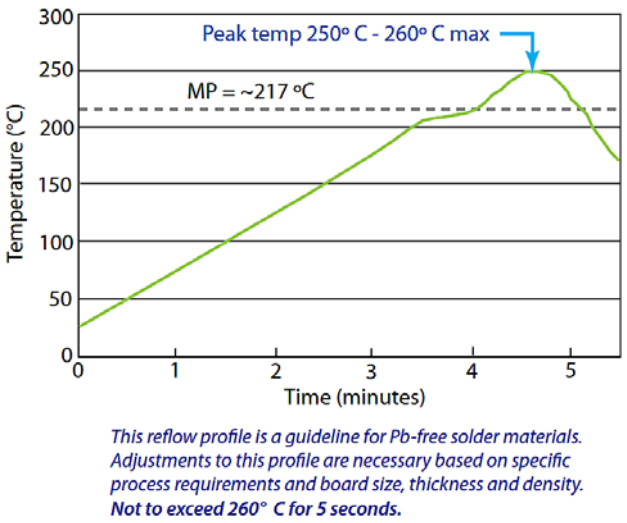



**Figure 6. Reflow Profile**

## ORIENTATION OF THE PTIC FOR OPTIMUM LOSSES

When configuring the PTIC in your specific circuit design, at least one of the RF terminals must be connected to DC ground. If minimum transition times are required, DC ground on both RF terminals is recommended. To minimize losses, the PTIC should be oriented such that RF2 is at the lower RF impedance of the two RF nodes. A shunt PTIC, for example, should have RF2 connected to RF ground.

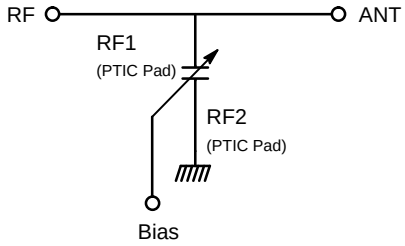



**Figure 7. PTIC Orientation Functional Block Diagram**

## PART NUMBER DEFINITION

**Table 4. PART NUMBERS**

| Part Number | Capacitance | | Marking | | Package* |
|---|---|---|---|---|---|
| | 2 V | 24 V | Device ID | Trace Code | |
| TCP−5039UB−DT | 3.90 | 0.839 | E | YW** | 6−bump WLCSP |

*See PTIC package dimensions on following page.
**Refer to table below (Table 5) for YW trace code.

For information on device numbering and ordering codes, please download the *Device Nomenclature* technical note (TND310/D) from www.onsemi.com.

**Table 5. Two Digits Year and Work Week Date coding (YW)** − In Process Product / Traceability Date Code Marking

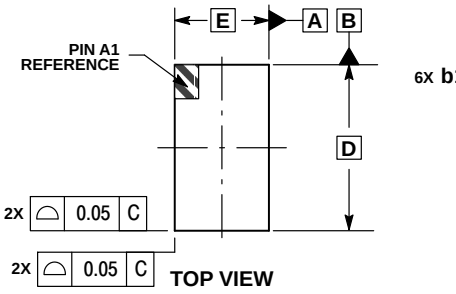
| Code | Term | Definition | | | | | | | | |
|---|---|---|---|---|---|---|---|---|---|---|
| YW | Year and Work Week | Two−character Alpha Code. Example: 2005, workweek 10 = GJ | | | | | | | | |
| | | YEAR | WORK WEEK | CODE | YEAR | WORK WEEK | CODE | YEAR | WORK WEEK | CODE |
| | | 2003 | 1<br>26<br>27<br>52 | CA<br>CZ<br>DA<br>DZ | 2004 | 1<br>26<br>27<br>52 | EA<br>EZ<br>FA<br>FZ | 2005 | 1<br>26<br>27<br>52 | GA<br>GZ<br>HA<br>HZ |
| | | 2006 | 1<br>26<br>27<br>52 | IA<br>IZ<br>JA<br>JZ | 2007 | 1<br>26<br>27<br>52 | KA<br>KZ<br>LA<br>LZ | 2008 | 1<br>26<br>27<br>52 | MA<br>MZ<br>NA<br>NZ |
| | | 2009 | 1<br>26<br>27<br>52 | PA<br>PZ<br>RA<br>RZ | 2010 | 1<br>26<br>27<br>52 | SA<br>SZ<br>TA<br>TZ | 2011 | 1<br>26<br>27<br>52 | UA<br>UZ<br>VA<br>VZ |
| | | 2012 | 1<br>26<br>27<br>52 | WA<br>WZ<br>XA<br>XZ | 2013 | 1<br>26<br>27<br>52 | YA<br>YZ<br>ZA<br>ZZ | 2014 | 1<br>26<br>27<br>52 | AA<br>AZ<br>BA<br>BZ |
| | | 2015 | 1<br>26<br>27<br>52 | CA<br>CZ<br>DA<br>DZ | 2016 | 1<br>26<br>27<br>52 | EA<br>EZ<br>FA<br>FZ | 2017 | 1<br>26<br>27<br>52 | GA<br>GZ<br>HA<br>HZ |

For dates outside of the table: the first character of the code is incremented at the start of workweek 01 and workweek 27 each year. The second character begins with “A” in workweek 01 of each year and increments weekly. “A” follows “Z” to make the code continuous.

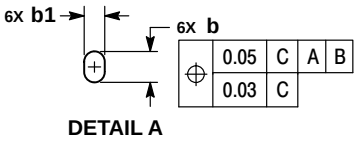
# TCP−5039UB

## PACKAGE DIMENSIONS

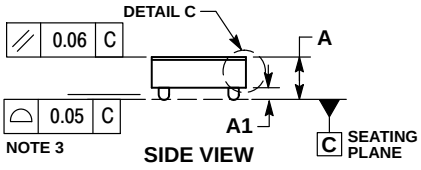
**WLCSP6, 1.097x0.622**
CASE 567NZ
ISSUE A



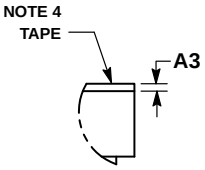

TOP VIEW



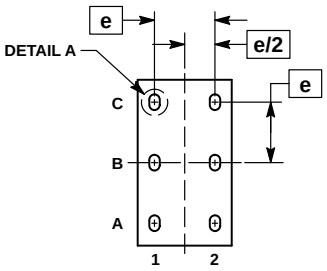

DETAIL A




SIDE VIEW




DETAIL C

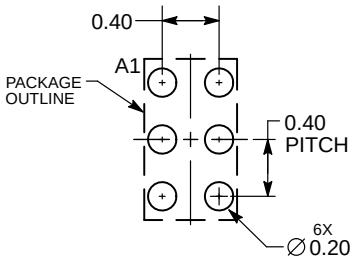



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.
4. BACKSIDE TAPE APPLIED TO IMPROVE PIN 1 MARKING.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | NOM | MAX |
| A | 0.295 | 0.335 | 0.375 |
| A1 | 0.065 | 0.090 | 0.115 |
| A3 | | 0.025 REF | |
| b | 0.125 | 0.150 | 0.175 |
| b1 | 0.075 | 0.100 | 0.125 |
| D | 1.047 | 1.097 | 1.147 |
| E | 0.572 | 0.622 | 0.672 |
| e | | 0.40 BSC | |

**RECOMMENDED SOLDERING FOOTPRINT***




DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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